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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



FEATURES

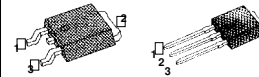
- ◆ Avalanche Rugged Technology
- ◆ Rugged Gate Oxide Technology
- ◆ Lower Input Capacitance
- ◆ Improved Gate Charge
- ◆ Extended Safe Operating Area
- ◆ Lower Leakage Current: 10µA (Max.) @ $V_{DS} = 200V$
- ◆ Lower $R_{DS(ON)}$: 1.185Ω (Typ.)

$$BV_{DSS} = 200 V$$

$$R_{DS(on)} = 1.5\Omega$$

$$I_D = 2.7 A$$

D-PAK **I-PAK**



1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	200	V
I_D	Continuous Drain Current ($T_C=25^\circ C$)	2.7	A
	Continuous Drain Current ($T_C=100^\circ C$)	1.7	
I_{DM}	Drain Current-Pulsed (1)	9	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (2)	24	mJ
I_{AR}	Avalanche Current (1)	2.7	A
E_{AR}	Repetitive Avalanche Energy (1)	2.1	mJ
dv/dt	Peak Diode Recovery dv/dt (3)	5	V/ns
P_D	Total Power Dissipation ($T_A=25^\circ C$) *	2.5	W
	Total Power Dissipation ($T_C=25^\circ C$)	21	W
	Linear Derating Factor	0.17	W/ $^\circ C$
T_J, T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8. from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	5.7	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient *	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

* When mounted on the minimum pad size recommended (PCB Mount).

Rev. B

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV _{DSS}	Drain-Source Breakdown Voltage	200	--	--	V	V _{GS} =0V, I _D =250μA
ΔBV/ΔT _J	Breakdown Voltage Temp. Coeff.	--	0.19	--	V/°C	I _D =250μA See Fig 7
V _{GS(th)}	Gate Threshold Voltage	1.0	--	2.0	V	V _{DS} =5V, I _D =250μA
I _{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V _{GS} =20V
	Gate-Source Leakage , Reverse	--	--	-100		V _{GS} =-20V
I _{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V _{DS} =200V
		--	--	100		V _{DS} =160V, T _C =125°C
R _{DS(on)}	Static Drain-Source On-State Resistance	--	--	1.5	Ω	V _{GS} =5V, I _D =1.35A (4)
g _{fs}	Forward Transconductance	--	1.9	--	∅	V _{DS} =40V, I _D =1.35A (4)
C _{iss}	Input Capacitance	--	185	240	pF	V _{GS} =0V, V _{DS} =25V, f =1MHz See Fig 5
C _{oss}	Output Capacitance	--	35	45		
C _{rss}	Reverse Transfer Capacitance	--	14	20		
t _{d(on)}	Turn-On Delay Time	--	9	30	ns	V _{DD} =100V, I _D =3.3A, R _G =22Ω See Fig 13 (4) (5)
t _r	Rise Time	--	9	30		
t _{d(off)}	Turn-Off Delay Time	--	20	50		
t _f	Fall Time	--	6	20		
Q _g	Total Gate Charge	--	6.1	9	nC	V _{DS} =160V, V _{GS} =5V, I _D =3.3A See Fig 6 & Fig 12 (4) (5)
Q _{gs}	Gate-Source Charge	--	1.4	--		
Q _{gd}	Gate-Drain (. Miller.) Charge	--	2.8	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I _S	Continuous Source Current	--	--	2.7	A	Integral reverse pn-diode in the MOSFET
I _{SM}	Pulsed-Source Current (1)	--	--	9		
V _{SD}	Diode Forward Voltage (4)	--	--	1.5	V	T _J =25°C, I _S =2.7A, V _{GS} =0V
t _{rr}	Reverse Recovery Time	--	123	--	ns	T _J =25°C, I _F =3.3A
Q _{rr}	Reverse Recovery Charge	--	0.38	--	μC	di _F /dt=100A/μs (4)

Notes;

- Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- L=5mH, I_{AS}=2.7A, V_{DD}=50V, R_G=27Ω, Starting T_J=25°C
- I_{SD} ≤ 3.3A, di/dt ≤ 140A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C
- Pulse Test: Pulse Width = 250μs, Duty Cycle ≤ 2%
- Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

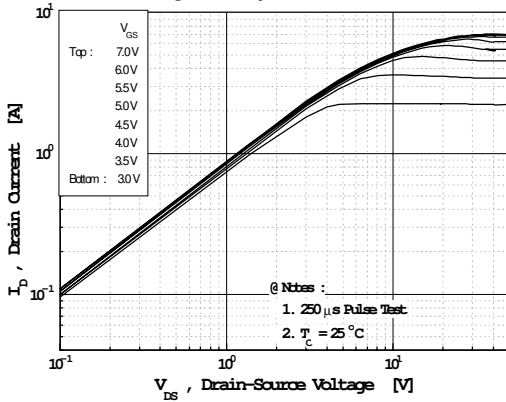


Fig 2. Transfer Characteristics

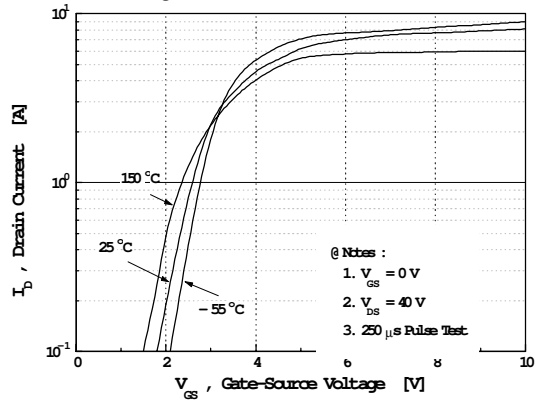


Fig 3. On-Resistance vs. Drain Current

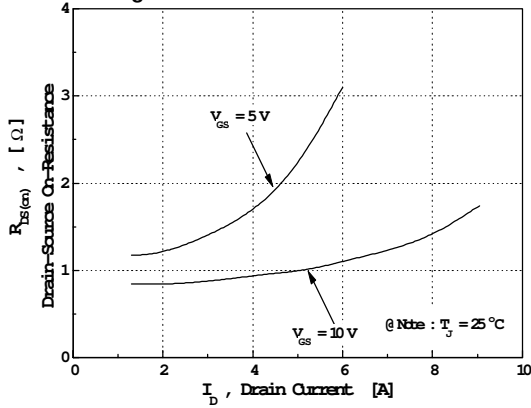


Fig 4. Source-Drain Diode Forward Voltage

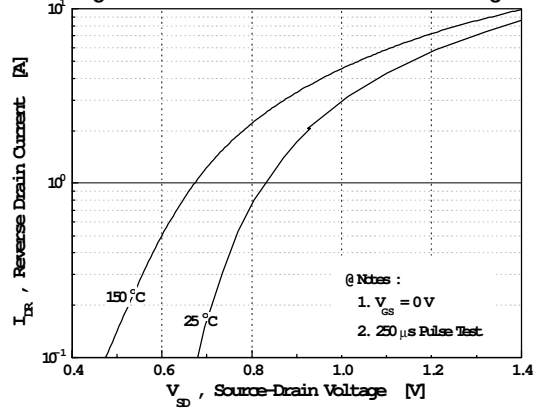


Fig 5. Capacitance vs. Drain-Source Voltage

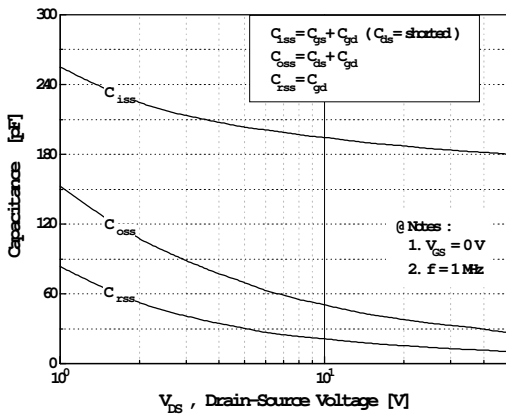


Fig 6. Gate Charge vs. Gate-Source Voltage

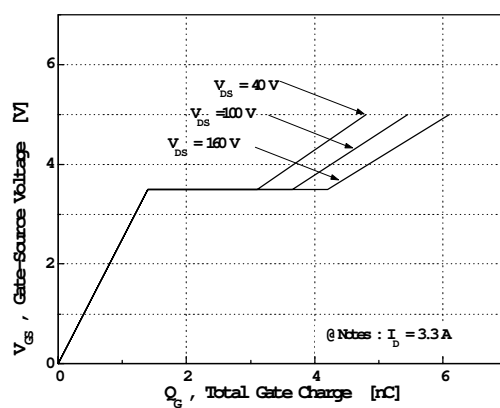


Fig 7. Breakdown Voltage vs. Temperature

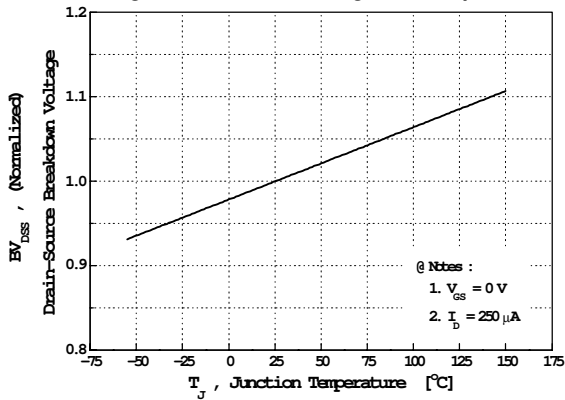


Fig 8. On-Resistance vs. Temperature

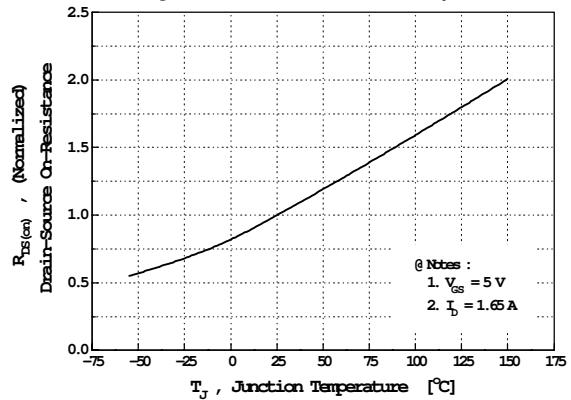


Fig 9. Max. Safe Operating Area

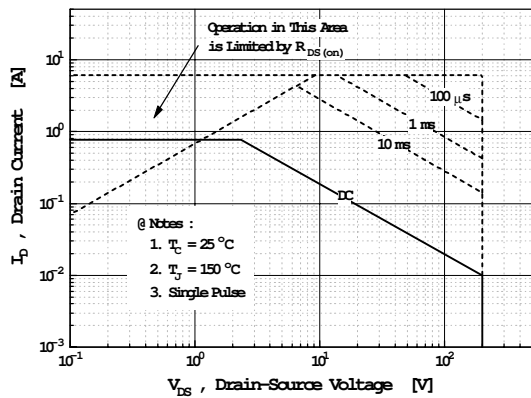


Fig 10. Max. Drain Current vs. Ambient Temperature

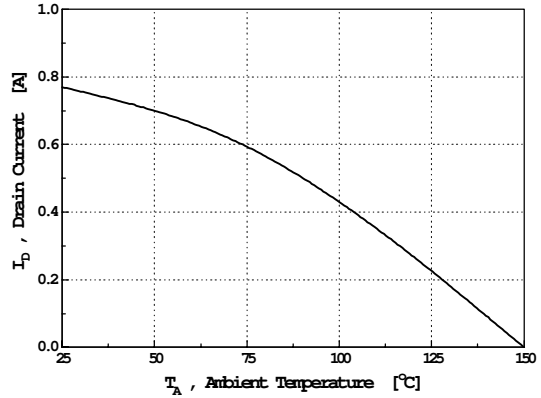


Fig 11. Thermal Response

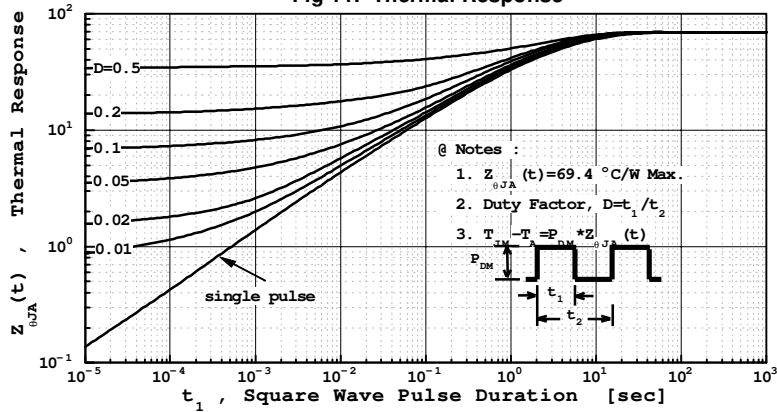


Fig 12. Gate Charge Test Circuit & Waveform

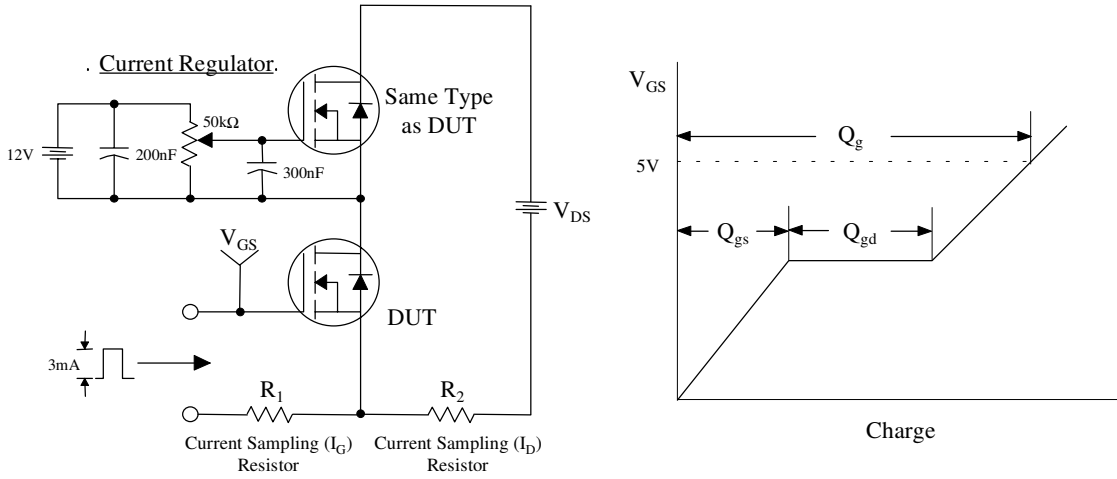


Fig 13. Resistive Switching Test Circuit & Waveforms

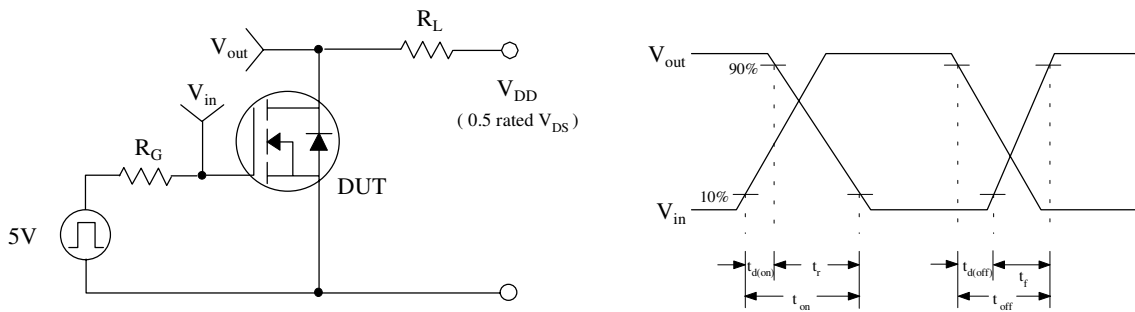


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

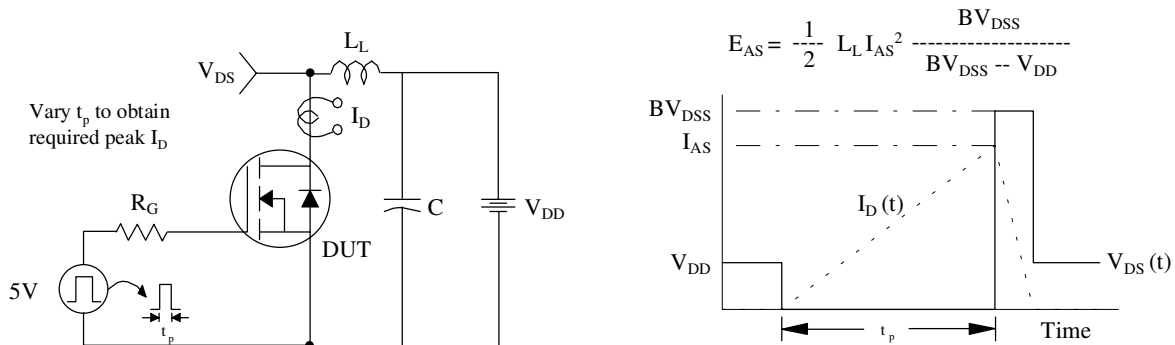
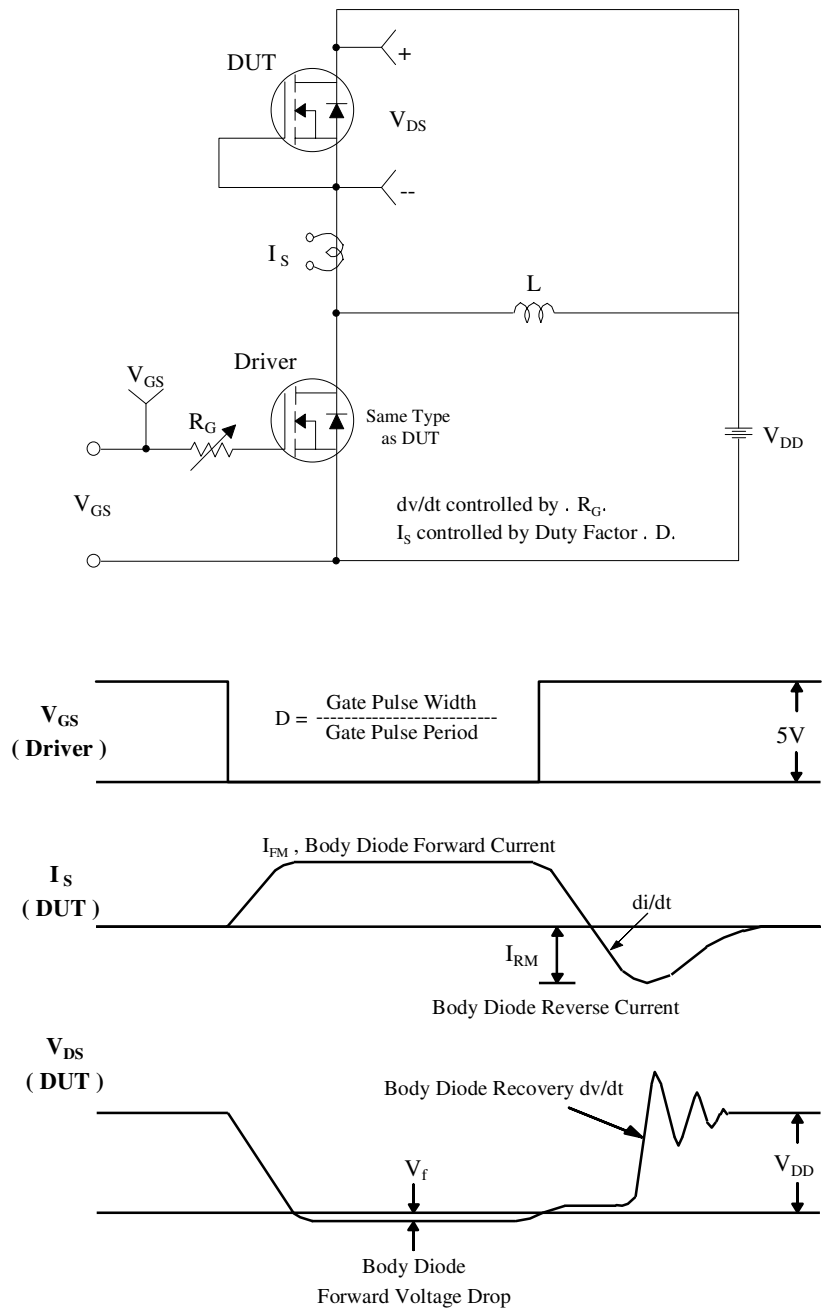


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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